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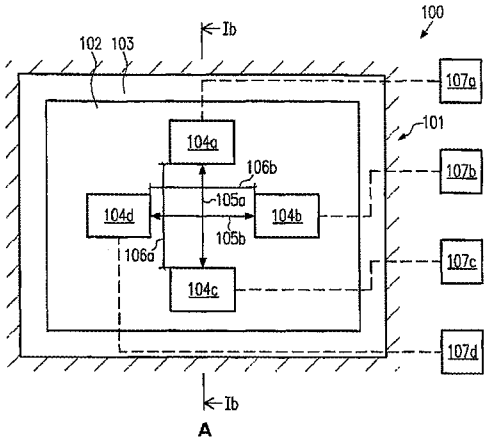
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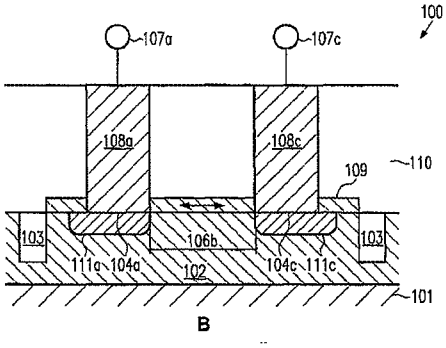
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(54) Title: TECHNIQUE FOR EVALUATING LOCAL ELECTRICAL CHARACTERISTICS IN SEMICONDUCTOR DEVICES





(57) Abstract: By providing a test structure (100) including a plurality of test pads (104), the anisotropic behavior of stress and strain influenced electrical characteristics, such as the electron mobility, may be determined in a highly efficient manner. Moreover, the test pads (104) may enable the detection of stress and strain induced modifications with a spatial resolution in the order of magnitude of individual circuit elements.

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